



■ **Block Diagram**

1. CMOS output product

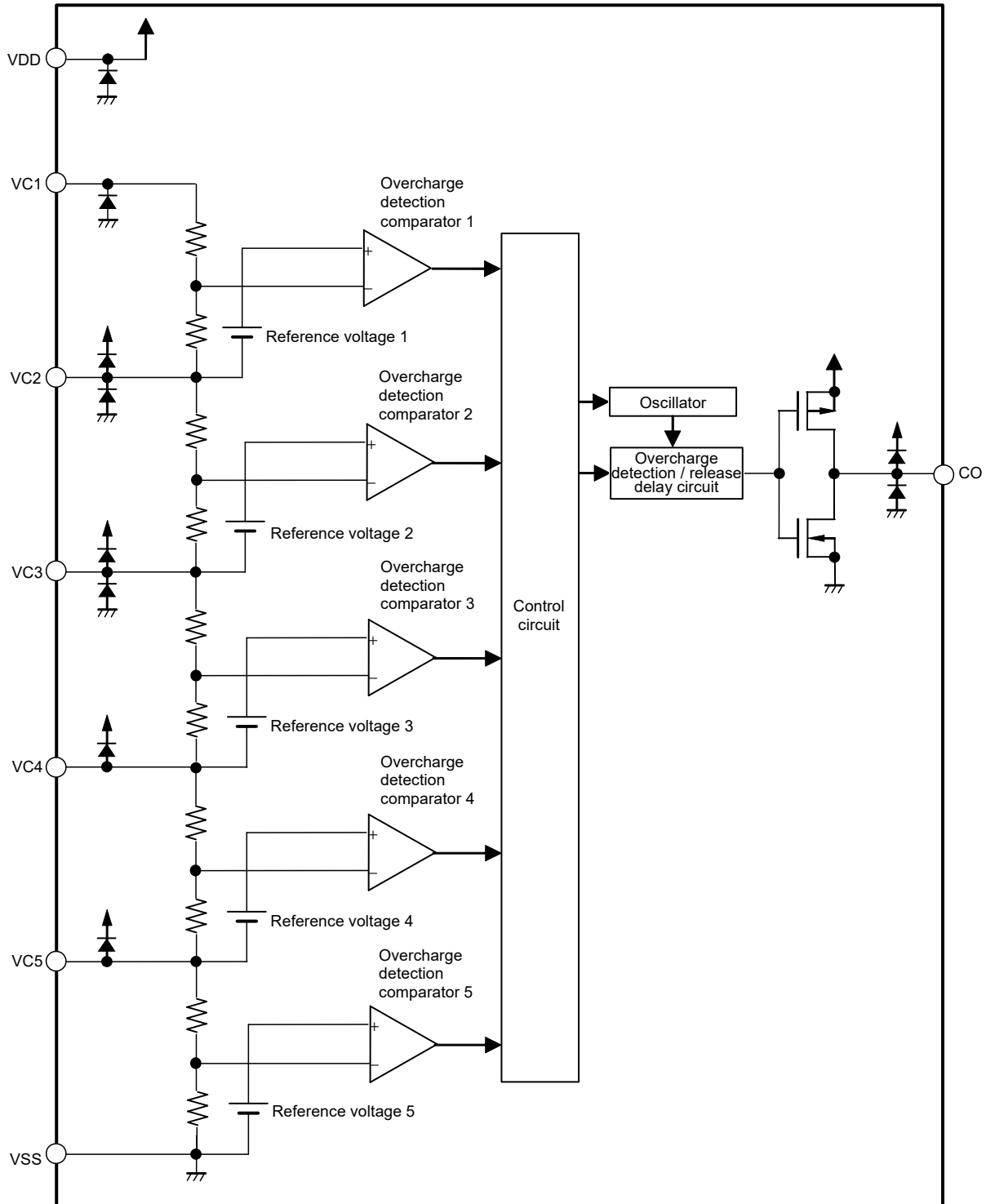


Figure 1

**Remark** The diodes in the figure are parasitic diodes.

2. Nch open-drain output product

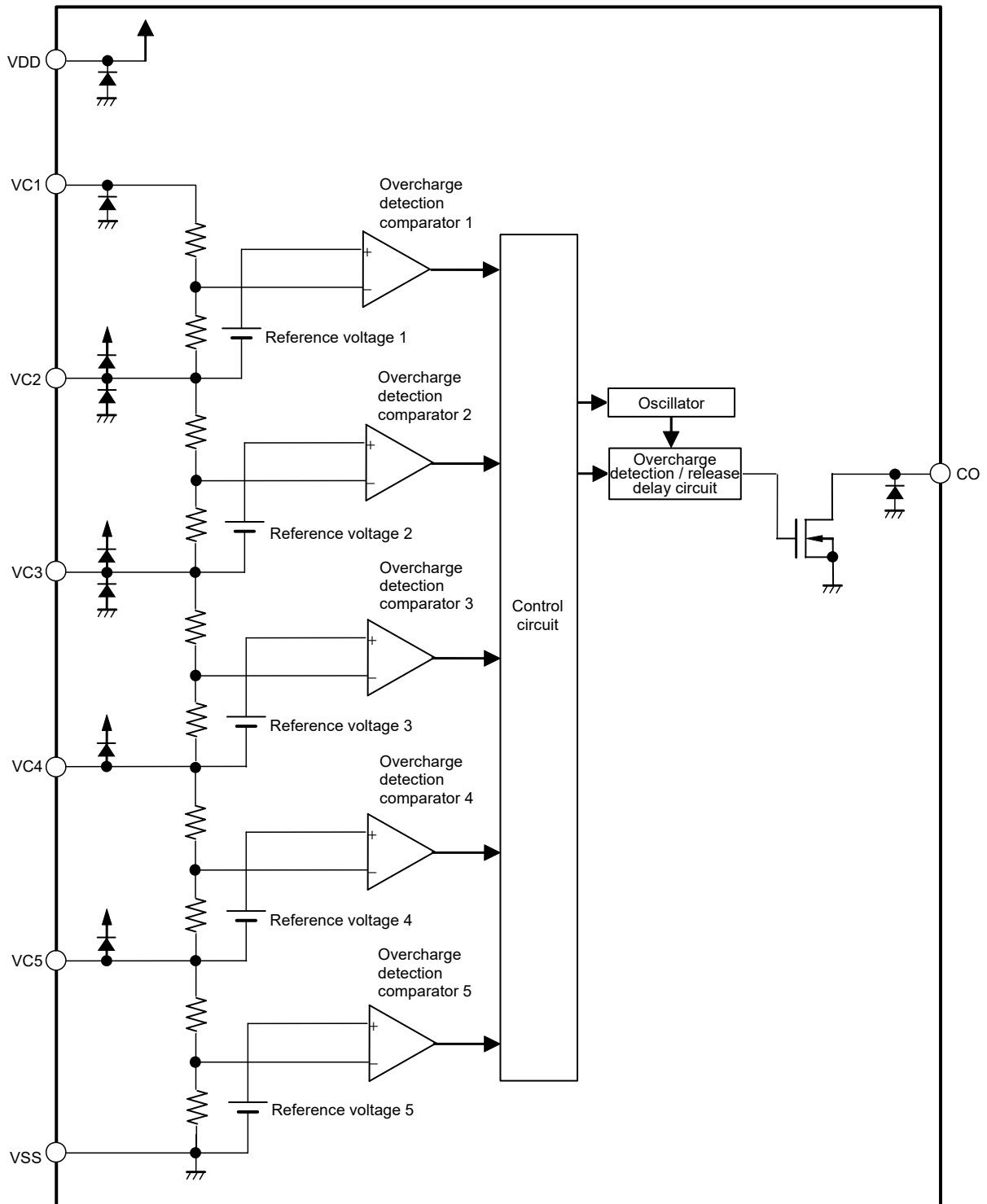
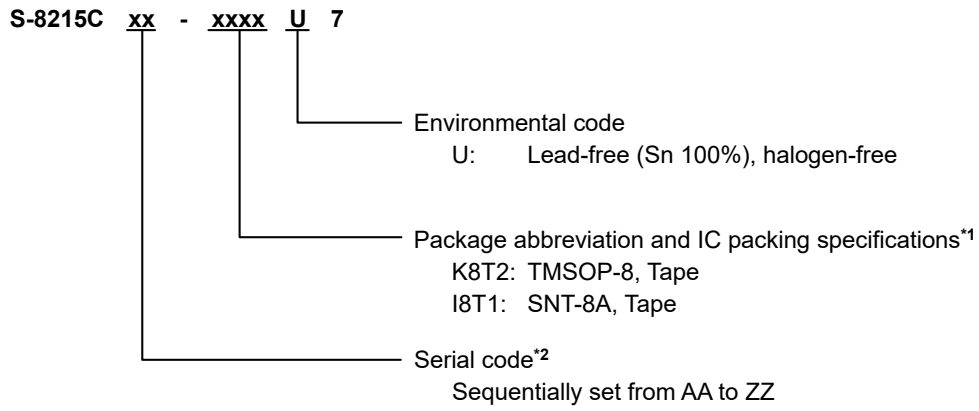


Figure 2

**Remark** The diodes in the figure are parasitic diodes.

■ **Product Name Structure**

1. **Product name**



\*1. Refer to the tape drawing.

\*2. Refer to "3. **Product name list**".

2. **Packages**

**Table 1 Package Drawing Codes**

Package Name	Dimension	Tape	Reel	Land
TMSOP-8	FM008-A-P-SD	FM008-A-C-SD	FM008-A-R-SD	-
SNT-8A	PH008-A-P-SD	PH008-A-C-SD	PH008-A-R-SD	PH008-A-L-SD

**3. Product name list**

**3.1 TMSOP-8**

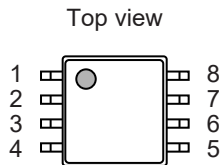
**Table 2**

Product Name	Overcharge Detection Voltage [V <sub>CU</sub> ]	Overcharge Release Voltage [V <sub>CL</sub> ]	Overcharge Detection Delay Time [t <sub>CU</sub> ]	Output Form	Output Logic
S-8215CAA-K8T2U7	4.325 V	4.275 V	8 s	CMOS output	Active "H"
S-8215CAB-K8T2U7	4.325 V	4.075 V	8 s	CMOS output	Active "H"

**Remark** Please contact our sales representatives for products other than the above.

■ **Pin Configurations**

**1. TMSOP-8**

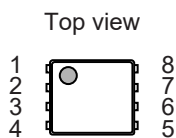


**Figure 3**

**Table 3**

Pin No.	Symbol	Description
1	VDD	Input pin for positive power supply
2	VC1	Positive voltage connection pin of battery 1
3	VC2	Negative voltage connection pin of battery 1, Positive voltage connection pin of battery 2
4	VC3	Negative voltage connection pin of battery 2, Positive voltage connection pin of battery 3
5	VC4	Negative voltage connection pin of battery 3, Positive voltage connection pin of battery 4
6	VC5	Negative voltage connection pin of battery 4, Positive voltage connection pin of battery 5
7	VSS	Input pin for negative power supply, Negative voltage connection pin of battery 5
8	CO	FET gate connection pin for charge control

**2. SNT-8A**



**Figure 4**

**Table 4**

Pin No.	Symbol	Description
1	VDD	Input pin for positive power supply
2	VC1	Positive voltage connection pin of battery 1
3	VC2	Negative voltage connection pin of battery 1, Positive voltage connection pin of battery 2
4	VC3	Negative voltage connection pin of battery 2, Positive voltage connection pin of battery 3
5	VC4	Negative voltage connection pin of battery 3, Positive voltage connection pin of battery 4
6	VC5	Negative voltage connection pin of battery 4, Positive voltage connection pin of battery 5
7	VSS	Input pin for negative power supply, Negative voltage connection pin of battery 5
8	CO	FET gate connection pin for charge control

■ Absolute Maximum Ratings

Table 5

(Ta = +25°C unless otherwise specified)

Item		Symbol	Applied Pin	Absolute Maximum Rating	Unit
Input voltage between VDD pin and VSS pin		V <sub>DS</sub>	VDD	V <sub>SS</sub> - 0.3 to V <sub>SS</sub> + 28	V
Input pin voltage		V <sub>IN</sub>	VC1	V <sub>SS</sub> - 0.3 to V <sub>SS</sub> + 28	V
			VC2, VC3	V <sub>SS</sub> - 0.3 to V <sub>DD</sub> + 0.3	V
			VC4, VC5	V <sub>DD</sub> - 28 to V <sub>DD</sub> + 0.3	V
CO pin output voltage	CMOS output product	V <sub>CO</sub>	CO	V <sub>SS</sub> - 0.3 to V <sub>DD</sub> + 0.3	V
	Nch open-drain output product			V <sub>SS</sub> - 0.3 to V <sub>SS</sub> + 28	V
Operation ambient temperature		T <sub>opr</sub>	-	-40 to +85	°C
Storage temperature		T <sub>stg</sub>	-	-40 to +125	°C

**Caution** The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

■ Thermal Resistance Value

Table 6

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	
Junction-to-ambient thermal resistance*1	θ <sub>JA</sub>	TMSOP-8	Board A	-	160	-	°C/W
			Board B	-	133	-	°C/W
			Board C	-	-	-	°C/W
			Board D	-	-	-	°C/W
			Board E	-	-	-	°C/W
		SNT-8A	Board A	-	211	-	°C/W
			Board B	-	173	-	°C/W
			Board C	-	-	-	°C/W
			Board D	-	-	-	°C/W
			Board E	-	-	-	°C/W

\*1. Test environment: compliance with JEDEC STANDARD JESD51-2A

**Remark** Refer to "■ Power Dissipation" and "Test Board" for details.

■ **Electrical Characteristics**

**Table 7**

(Ta = +25°C unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	Test Circuit
<b>Detection voltage</b>							
Overcharge detection voltage n (n = 1, 2, 3, 4, 5)	V <sub>CU<sub>n</sub></sub>	Ta = +25°C	V <sub>CU</sub> - 0.020	V <sub>CU</sub>	V <sub>CU</sub> + 0.020	V	1
		Ta = -10°C to +60°C*1	V <sub>CU</sub> - 0.025	V <sub>CU</sub>	V <sub>CU</sub> + 0.025	V	1
Overcharge release voltage n (n = 1, 2, 3, 4, 5)	V <sub>CL<sub>n</sub></sub>	-	V <sub>CL</sub> - 0.050	V <sub>CL</sub>	V <sub>CL</sub> + 0.050	V	1
<b>Input voltage</b>							
Operation voltage between VDD pin and VSS pin	V <sub>DSOP</sub>	-	3.6	-	26	V	-
<b>Input current</b>							
Current consumption during operation	I <sub>OPE</sub>	V1 = V2 = V3 = V4 = V5 = V <sub>CU</sub> × 0.75 V	-	0.3	0.7	μA	2
Current consumption during overdischarge	I <sub>OPED</sub>	V1 = V2 = V3 = V4 = V5 = V <sub>CU</sub> × 0.4 V	-	0.05	0.30	μA	2
VC1 pin input current	I <sub>VC1</sub>	V1 = V2 = V3 = V4 = V5 = V <sub>CU</sub> × 0.75 V	-	-	0.3	μA	3
VCn pin input current (n = 2, 3, 4, 5)	I <sub>VCn</sub>	V1 = V2 = V3 = V4 = V5 = V <sub>CU</sub> × 0.75 V	-0.3	0.0	0.3	μA	3
<b>Output current</b>							
CO pin source current	I <sub>COH</sub>	-	-	-	-20	μA	4
CO pin sink current	I <sub>COL</sub>	CMOS output product	0.4	-	-	mA	4
CO pin leakage current	I <sub>COLL</sub>	Nch open-drain output product	-	-	0.1	μA	4
<b>Delay time</b>							
Overcharge detection delay time	t <sub>CU</sub>	-	t <sub>CU</sub> × 0.8	t <sub>CU</sub>	t <sub>CU</sub> × 1.2	s	1
Overcharge timer reset delay time	t <sub>TR</sub>	-	6	12	20	ms	1
Transition time to test mode	t <sub>TST</sub>	-	-	-	10	ms	1

\*1. Since products are not screened at high and low temperature, the specification for this temperature range is guaranteed by design, not tested in production.



## ■ Test Circuits

### 1. Overcharge detection voltage n ( $V_{CU_n}$ ), overcharge release voltage n ( $V_{CL_n}$ ) (Test circuit 1)

After setting  $V_0 = 0\text{ V}$ ,  $V_1$  to  $V_5 = V_{CU} - 0.05\text{ V}$ ,  $V_1$  is gradually increased. When the CO pin output inverts, the voltage  $V_1$  is defined as  $V_{CU1}$ .

$V_0$  is then returned to  $0\text{ V}$ . After setting  $V_1 = V_{CU} + 0.05\text{ V}$ ,  $V_2$  to  $V_5 = V_{CL} - 0.05\text{ V}$ ,  $V_1$  is gradually decreased. When the CO pin output inverts again, the voltage  $V_1$  is defined as  $V_{CL1}$ .

$V_{CU_n}$  and  $V_{CL_n}$  ( $n = 2$  to  $5$ ) can be defined in the same way as when  $n = 1$ .

### 2. Output current (Test circuit 4)

#### 2.1 CMOS output product

SW1 and SW2 are set to OFF.

##### 2.1.1 Active "H"

###### (1) CO pin source current ( $I_{COH}$ )

After setting  $V_0 = 0\text{ V}$ ,  $V_1 = 4.8\text{ V}$ ,  $V_2$  to  $V_5 = 2.05\text{ V}$  and  $V_6 = 0.5\text{ V}$ , SW1 is turned on.  $I_6$  is then defined as  $I_{COH}$ .

###### (2) CO pin sink current ( $I_{COL}$ )

After setting  $V_0 = 0\text{ V}$ ,  $V_1$  to  $V_5 = 2.6\text{ V}$  and  $V_7 = 0.5\text{ V}$ , SW2 is turned on.  $I_7$  is then defined as  $I_{COL}$ .

##### 2.1.2 Active "L"

###### (1) CO pin source current ( $I_{COH}$ )

After setting  $V_0 = 0\text{ V}$ ,  $V_1$  to  $V_5 = 2.6\text{ V}$  and  $V_6 = 0.5\text{ V}$ , SW1 is turned on.  $I_6$  is then defined as  $I_{COH}$ .

###### (2) CO pin sink current ( $I_{COL}$ )

After setting  $V_0 = 0\text{ V}$ ,  $V_1 = 4.8\text{ V}$ ,  $V_2$  to  $V_5 = 2.05\text{ V}$  and  $V_7 = 0.5\text{ V}$ , SW2 is turned on.  $I_7$  is then defined as  $I_{COL}$ .

## 2.2 Nch open-drain output product

SW1 and SW2 are set to OFF.

### 2.2.1 Active "H"

#### (1) CO pin leakage current "L" ( $I_{COLL}$ )

After setting  $V_0 = 0$  V,  $V_1 = 4.8$  V,  $V_2$  to  $V_5 = 2.05$  V and  $V_7 = 28$  V, SW2 is turned on.  $I_7$  is then defined as  $I_{COLL}$ .

#### (2) CO pin sink current ( $I_{COL}$ )

After setting  $V_0 = 0$  V,  $V_1$  to  $V_5 = 2.6$  V and  $V_7 = 0.5$  V, SW2 is turned on.  $I_7$  is then defined as  $I_{COL}$ .

### 2.2.2 Active "L"

#### (1) CO pin leakage current "L" ( $I_{COLL}$ )

After setting  $V_0 = 0$  V,  $V_1$  to  $V_5 = 2.6$  V,  $V_7 = 28$  V, SW2 is turned on.  $I_7$  is then defined as  $I_{COLL}$ .

#### (2) CO pin sink current ( $I_{COL}$ )

After setting  $V_0 = 0$  V,  $V_1 = 4.8$  V,  $V_2$  to  $V_5 = 2.05$  V and  $V_7 = 0.5$  V, SW2 is turned on.  $I_7$  is then defined as  $I_{COL}$ .

## 3. Overcharge detection delay time ( $t_{CU}$ ) (Test circuit 1)

After setting  $V_0 = 0$  V,  $V_1$  to  $V_5 = 2.6$  V,  $V_1$  is increased to 4.8 V. The time interval from this increase until the CO pin output inverts is  $t_{CU}$ .

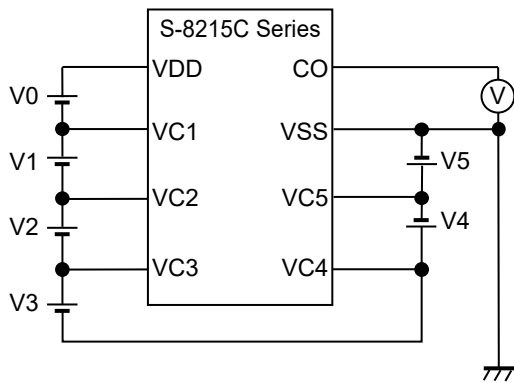
## 4. Overcharge timer reset delay time ( $t_{TR}$ ) (Test circuit 1)

After setting  $V_0 = 0$  V,  $V_1$  to  $V_5 = 2.6$  V,  $V_1$  is increased to 4.8 V (first rise) and decreased to 2.6 V ( $V_1$  fall) within  $t_{CU}$ . After that,  $V_1$  is increased to 4.8 V again (second rise), and measure the time interval until the CO pin output inverts. When the time interval from  $V_1$  fall until the second rise is short, the CO pin output inverts when  $t_{CU}$  has elapsed since the first rise. However, if the time interval is gradually made longer, CO pin output inverts when  $t_{CU}$  has elapsed since the second rise. The time interval from  $V_1$  fall until the second rise at that time is  $t_{TR}$ .

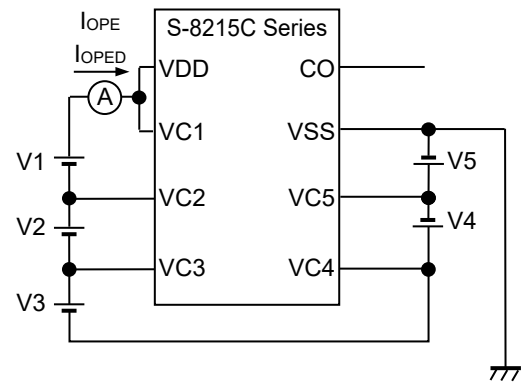
## 5. Transition time to test mode ( $t_{TST}$ ) (Test circuit 1)

After setting  $V_0 = 0$  V,  $V_1$  to  $V_5 = 2.6$  V,  $V_0$  is increased to 4.0 V and decreased to 0 V again.

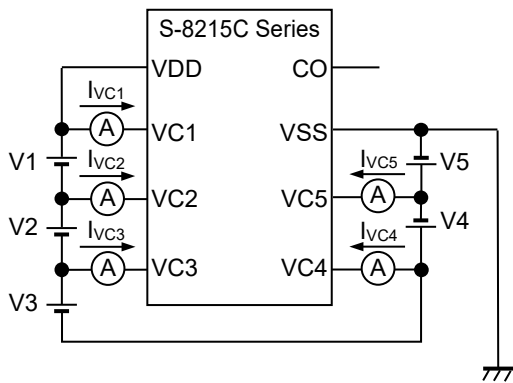
When the time interval from when  $V_0$  is increased until it is decreased is long, if  $V_1$  is then increased to 4.8 V, the CO pin output inverts within 40 ms. However, when the time interval from when  $V_0$  is increased until it is decreased is short, if  $V_1$  is then increased to 4.8 V, it takes more than 40 ms for the CO pin output to invert.  $t_{TST}$  is the minimum value of the time interval from  $V_0$  rise until  $V_0$  fall under the condition that the CO pin output inverts within 40 ms.



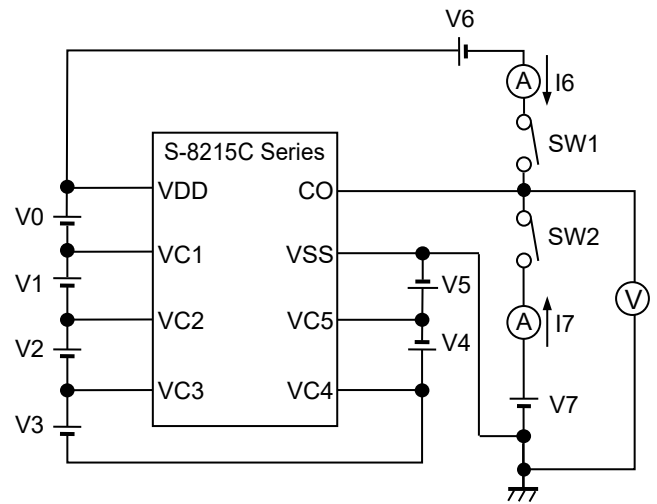
**Figure 5 Test Circuit 1**



**Figure 6 Test Circuit 2**



**Figure 7 Test Circuit 3**



**Figure 8 Test Circuit 4**

## ■ Operation

**Remark** Refer to "■ Battery Protection IC Connection Examples".

### 1. Normal status

When the voltage of all batteries is lower than overcharge release voltage  $n$  ( $V_{CLn}$ ), "L" (Active "H") or "H" (Active "L") is output from the CO pin. This is the normal status.

### 2. Overcharge status

When the voltage of any of all batteries exceeds the overcharge detection voltage  $n$  ( $V_{CU_n}$ ) during charging in the normal status and the conditions continue for the overcharge detection delay time ( $t_{CU}$ ) or longer, the CO pin output inverts. This is the overcharge status. Connecting FET to the CO pin provides charge control and a second protection. When the voltage of all batteries falls below  $V_{CLn}$  and the conditions continue for 2.0 ms typ. or longer, the S-8215C Series returns to the normal status.

### 3. Overcharge timer reset function

During  $t_{CU}$ , which is from when the voltage of any of the batteries being charged exceeds  $V_{CU_n}$  until charging stops, S-8215C Series has the following operations.

Even if an overcharge release noise, which temporarily forces the battery voltage below  $V_{CU_n}$ , is input,  $t_{CU}$  is continuously counted as long as the overcharge release noise time is shorter than the overcharge timer reset delay time ( $t_{TR}$ ). Under the same conditions, if the overcharge release noise time is  $t_{TR}$  or longer, counting of  $t_{CU}$  is reset once. After that, when  $V_{CU_n}$  has been exceeded, counting of  $t_{CU}$  resumes.

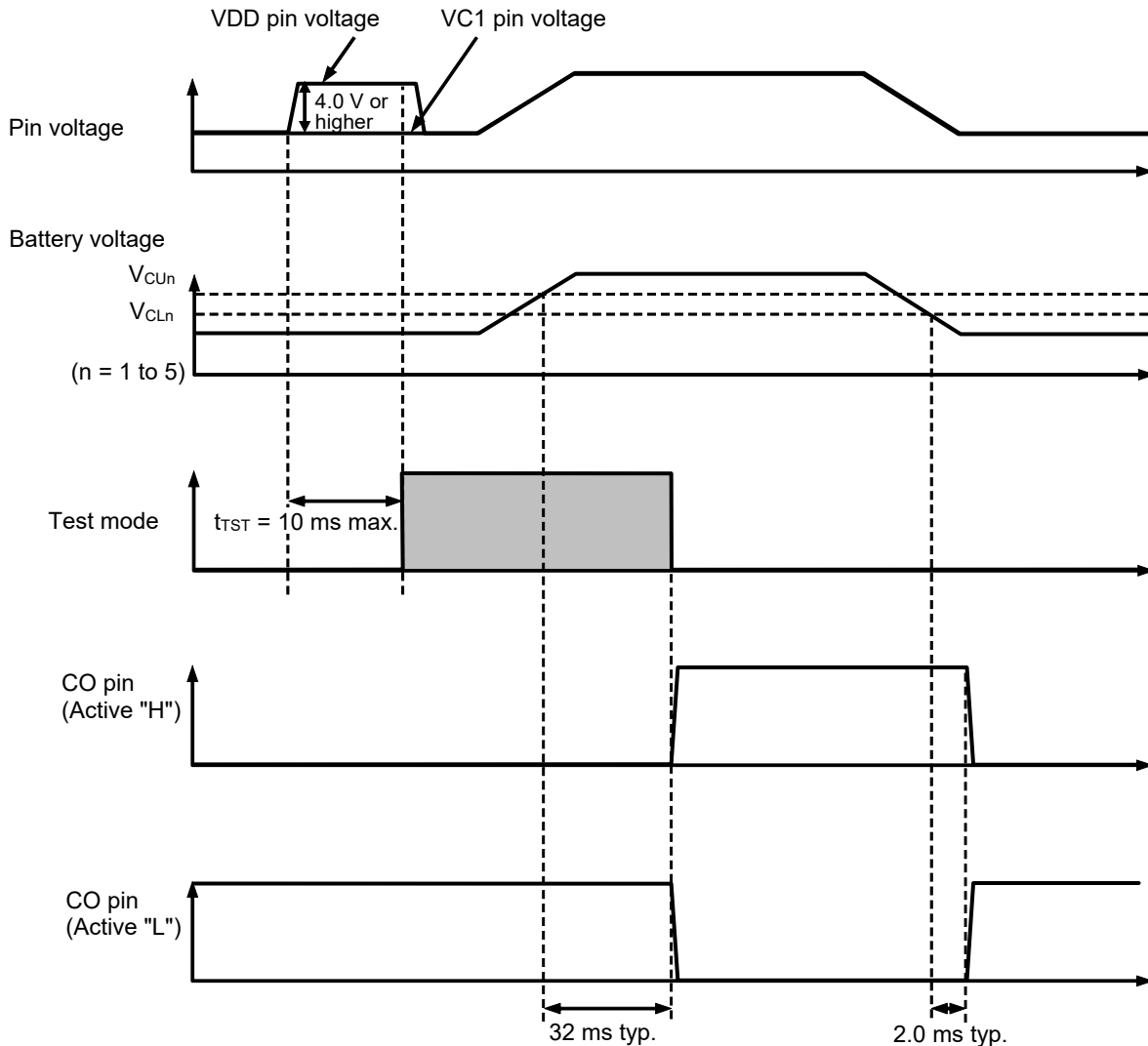
**Remark**  $n = 1$  to 5

**4. Test mode**

$t_{CU}$  can be shortened by transitioning to the test mode.

S-8215C Series transitions to the test mode by retaining the VDD pin voltage at 4.0 V above the VC1 pin voltage or higher for at least transition time to test mode ( $t_{TST}$ ). The status is retained by the internal latch and the test mode is retained even if the VDD pin voltage is decreased to the same voltage as that of the VC1 pin voltage.

After that, when S-8215C Series becomes the overcharge status, the test mode retaining latch is reset and the S-8215C Series is released from the test mode.

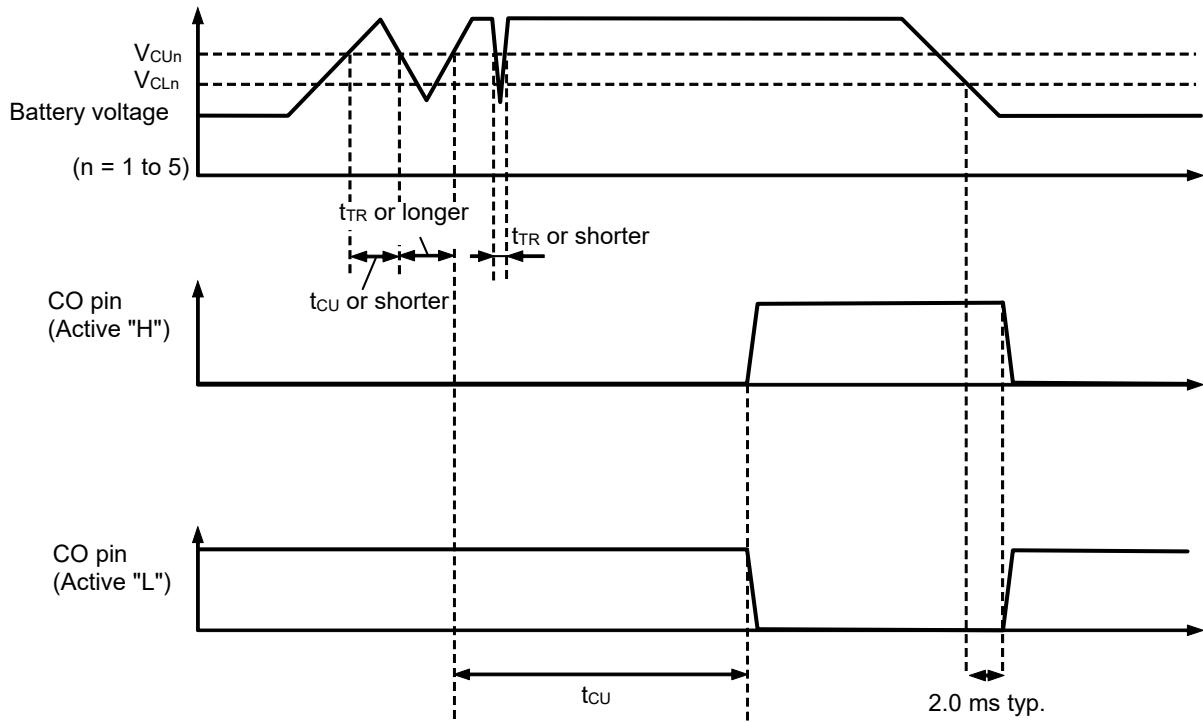


- Caution**
1. Transition to test mode when the voltage of all batteries is lower than  $V_{CUn}$ .
  2. The overcharge timer reset delay time ( $t_{TR}$ ) is not shortened in the test mode.

Figure 9

■ **Timing Charts**

1. **Overcharge detection operation**



**Figure 10**

2. Overcharge timer reset function

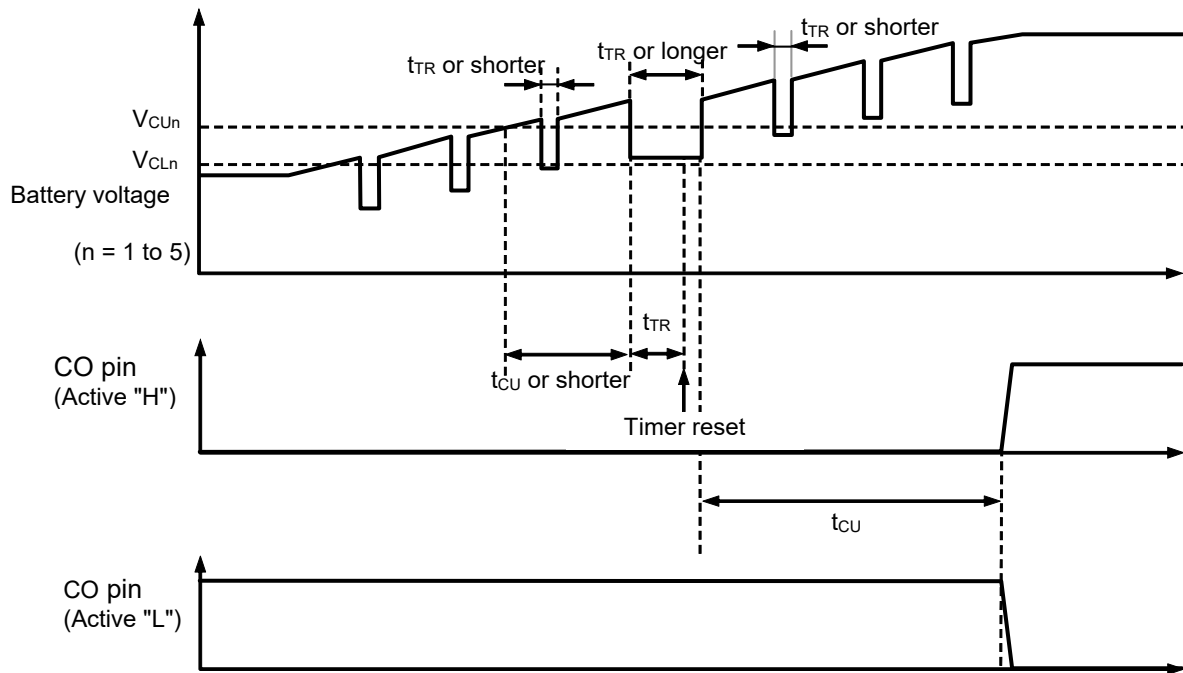


Figure 11

■ Battery Protection IC Connection Examples

1. 5-serial cell (CMOS output product)

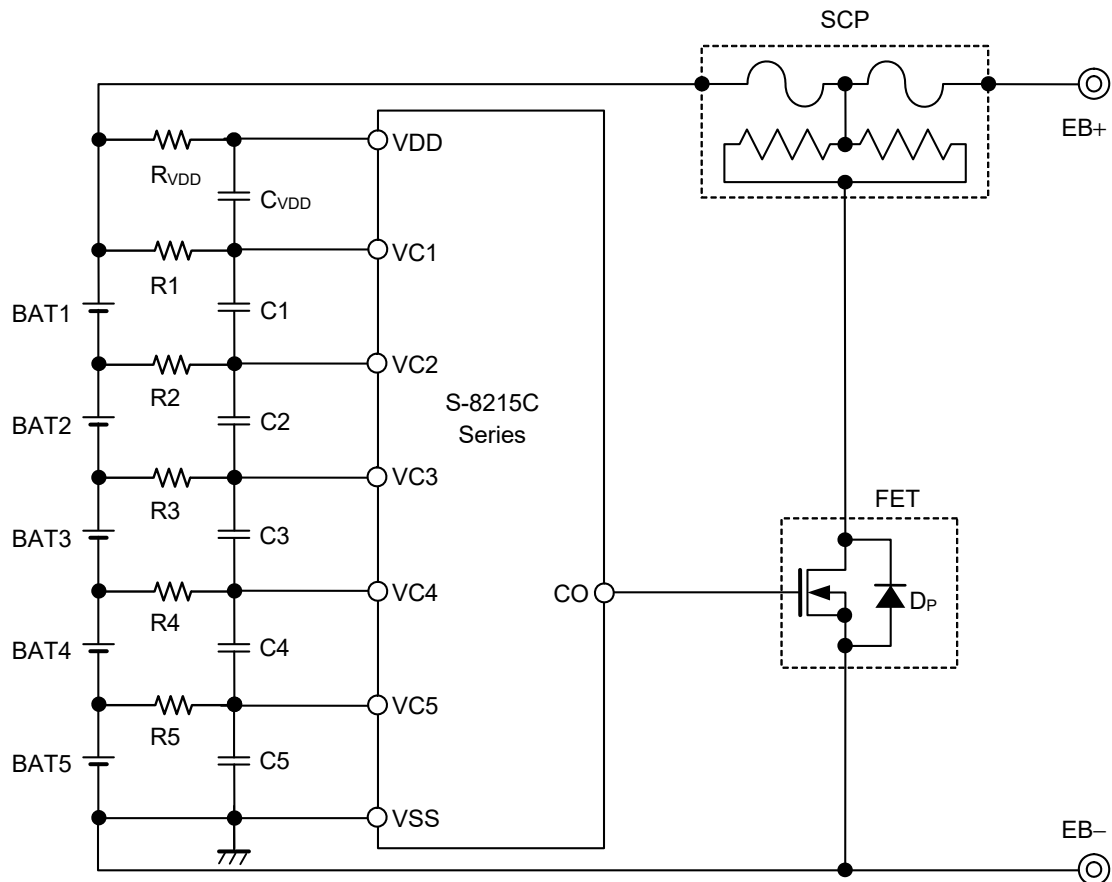


Figure 12

Table 8 Constants for External Components

No.	Symbol	Min.	Typ.	Max.	Unit
1	R1 to R5	100	1000	1000	$\Omega$
2	C1 to C5, $C_{VDD}$	0.1	0.1	1	$\mu F$
3	$R_{VDD}$	100	100	1000	$\Omega$

- Caution**
1. The constants may be changed without notice.
  2. It has not been confirmed whether the operation is normal or not in circuits other than the connection example. In addition, the connection example and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constants.
  3. R1 to R5 should be the same constant. C1 to C5 and  $C_{VDD}$  should be the same constant.



2. 4-serial cell (CMOS output product)

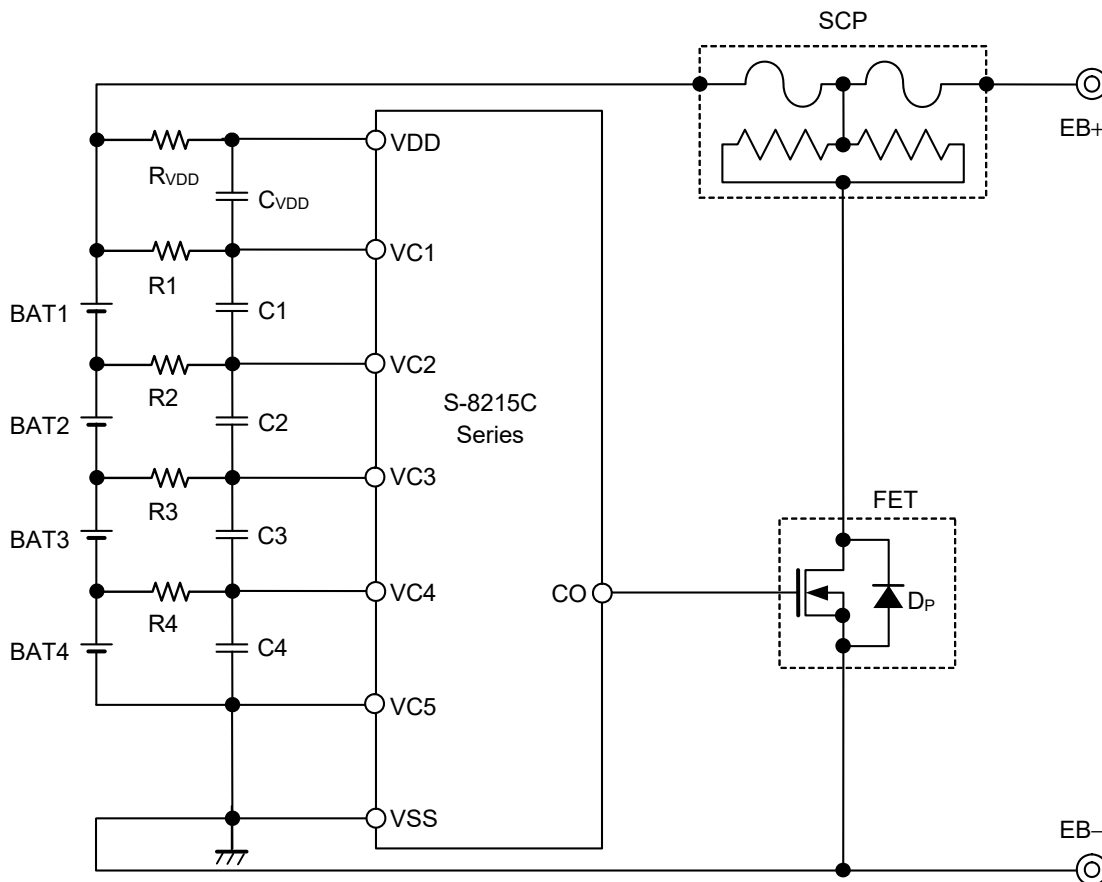


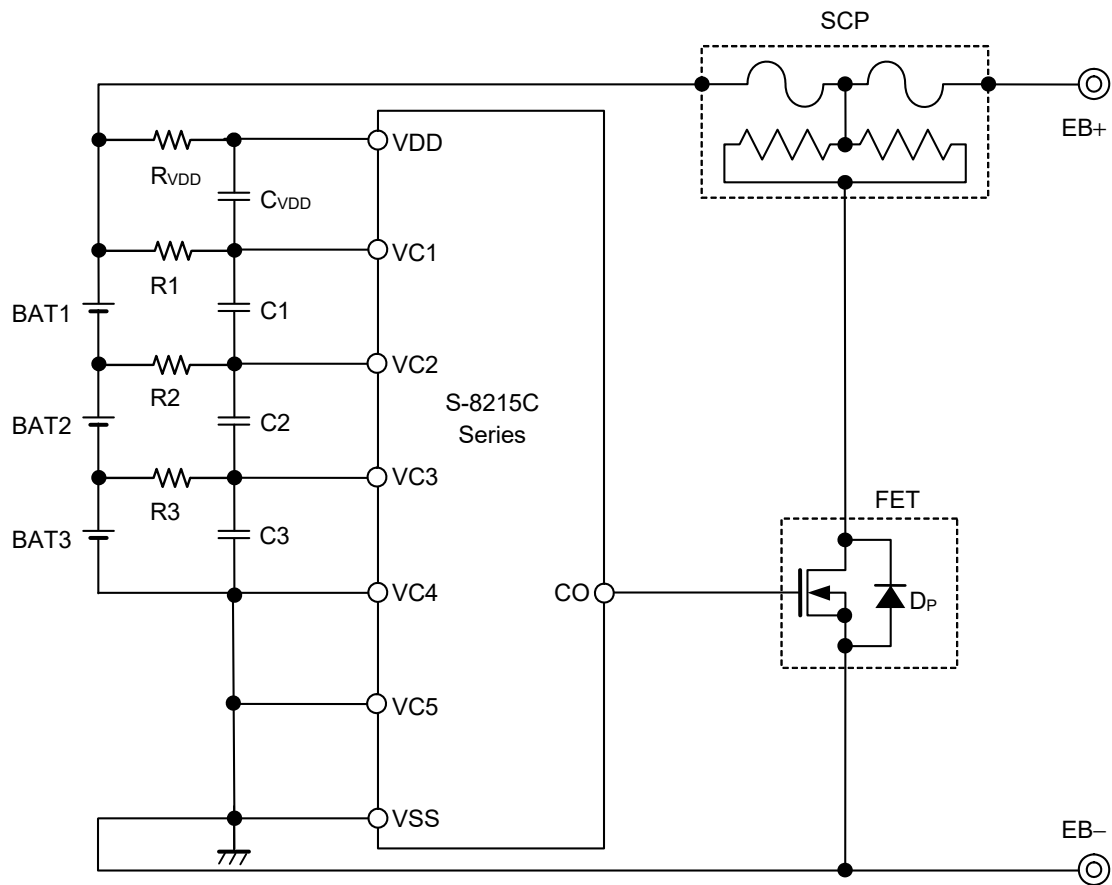
Figure 13

Table 9 Constants for External Components

No.	Symbol	Min.	Typ.	Max.	Unit
1	R1 to R4	100	1000	1000	$\Omega$
2	C1 to C4, $C_{VDD}$	0.1	0.1	1	$\mu F$
3	$R_{VDD}$	100	100	1000	$\Omega$

- Caution**
1. The constants may be changed without notice.
  2. It has not been confirmed whether the operation is normal or not in circuits other than the connection example. In addition, the connection example and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constants.
  3. R1 to R4 should be the same constant. C1 to C4 and  $C_{VDD}$  should be the same constant.

**3. 3-serial cell (CMOS output product)**



**Figure 14**

**Table 10 Constants for External Components**

No.	Symbol	Min.	Typ.	Max.	Unit
1	R1 to R3	100	1000	1000	Ω
2	C1 to C3, C <sub>VDD</sub>	0.1	0.1	1	μF
3	R <sub>VDD</sub>	100	100	1000	Ω

- Caution**
1. The constants may be changed without notice.
  2. It has not been confirmed whether the operation is normal or not in circuits other than the connection example. In addition, the connection example and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constants.
  3. R1 to R3 should be the same constant. C1 to C3 and C<sub>VDD</sub> should be the same constant.

**[For SCP, contact]**

Global Sales & Marketing Division, Dexerials Corporation  
Gate City Osaki East Tower 8F, 1-11-2  
Osaki, Shinagawa-ku, Tokyo, 141-0032, Japan  
TEL +81-3-5435-3946  
Contact Us: <http://www.dexerials.jp/en/>

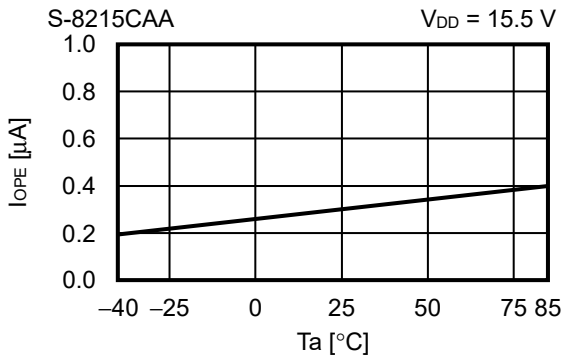
**■ Precautions**

- Do not connect batteries charged with  $V_{CLn}$  or higher. If the connected batteries include a battery charged with  $V_{CLn}$  or higher, the S-8215C Series may become overcharge status after all pins are connected.
- In some application circuits, even if an overcharged battery is not included, the order of connecting batteries may be restricted to prevent transient output of CO detection pulses when the batteries are connected. Perform thorough evaluation with the actual application circuit.
- Before the battery connection, short-circuit the battery side pins  $R_{VDD}$  and R1, shown in the figure in "**■ Battery Protection IC Connection Examples**".
- The application conditions for the input voltage, output voltage, and load current should not exceed the power dissipation.
- Do not apply to this IC an electrostatic discharge that exceeds the performance ratings of the built-in electrostatic protection circuit.
- ABLIC Inc. claims no responsibility for any disputes arising out of or in connection with any infringement of patents owned by a third party by products including this IC.

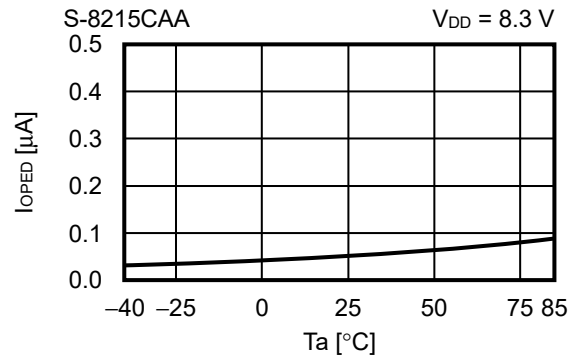
■ **Characteristics (Typical Data)**

**1. Current consumption**

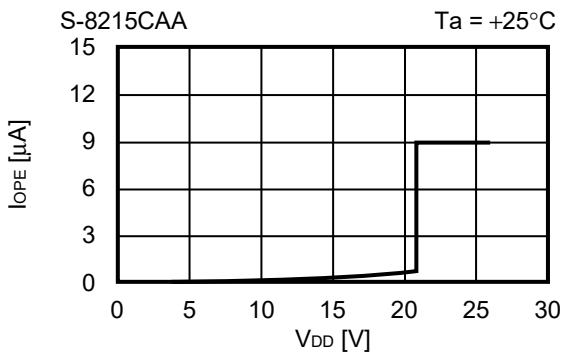
**1.1 I<sub>OPe</sub> vs. T<sub>a</sub>**



**1.2 I<sub>OPeD</sub> vs. T<sub>a</sub>**

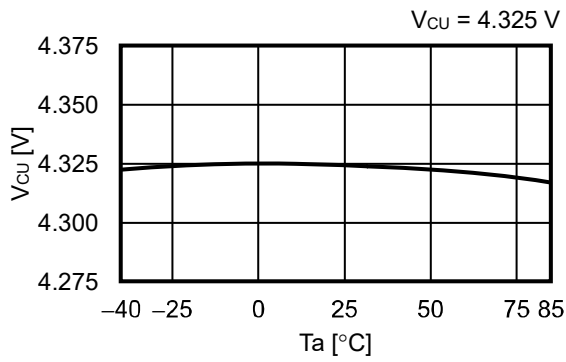


**1.3 I<sub>OPe</sub> vs. V<sub>DD</sub>**

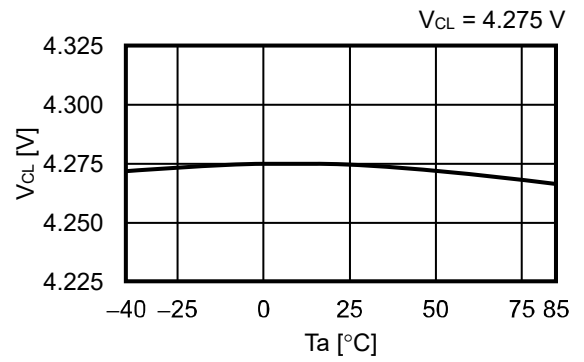


**2. Detection voltage**

**2.1  $V_{CU}$  vs.  $T_a$**

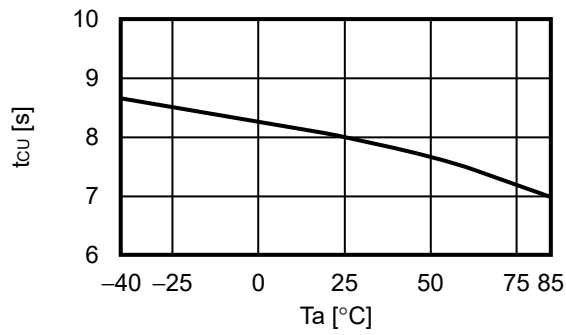


**2.2  $V_{CL}$  vs.  $T_a$**



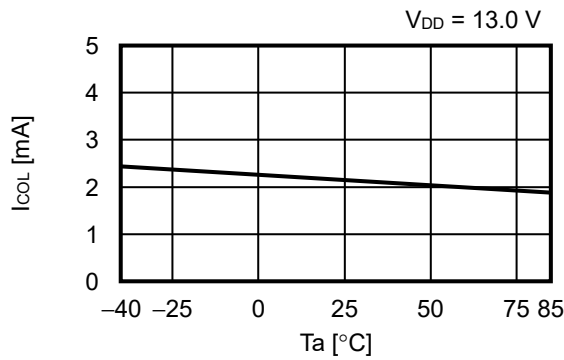
**3. Delay time**

**3.1  $t_{CU}$  vs.  $T_a$**

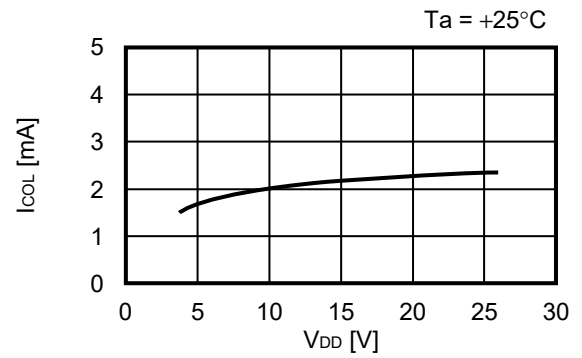


**4. Output current**

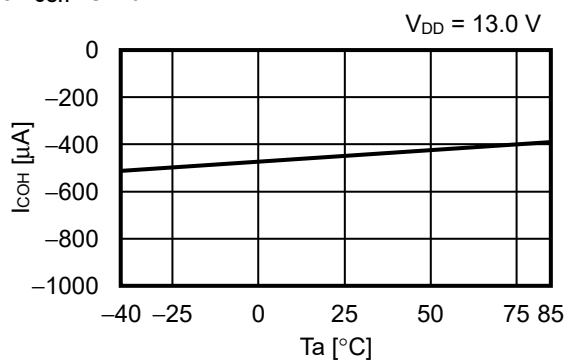
**4. 1 I<sub>COL</sub> vs. Ta**



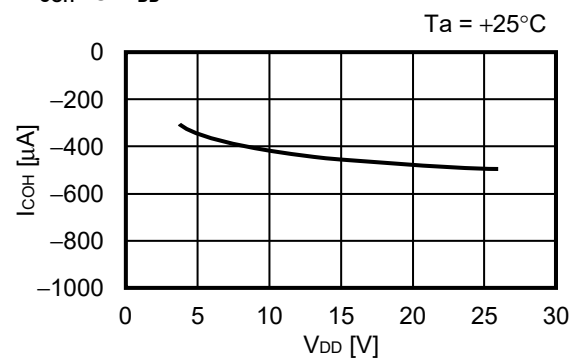
**4. 2 I<sub>COL</sub> vs. V<sub>DD</sub>**



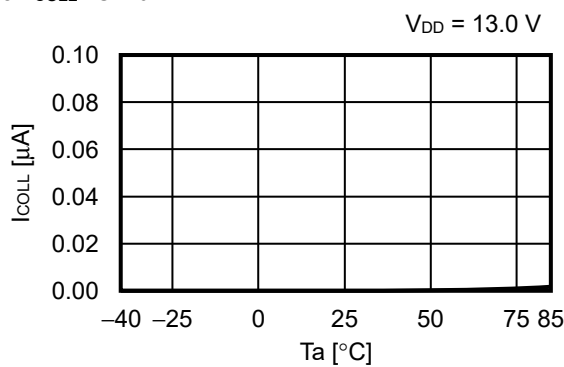
**4. 3 I<sub>COH</sub> vs. Ta**



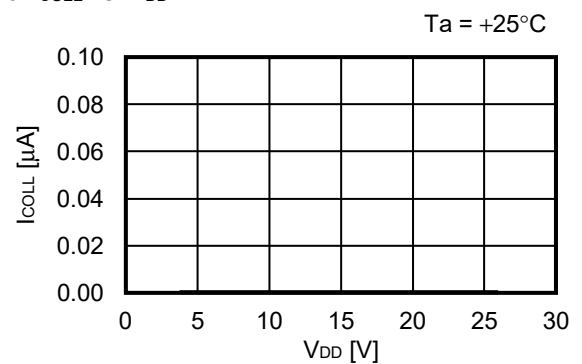
**4. 4 I<sub>COH</sub> vs. V<sub>DD</sub>**



**4. 5 I<sub>COLL</sub> vs. Ta**

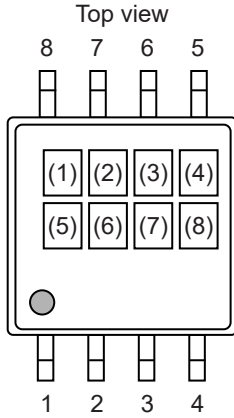


**4. 6 I<sub>COLL</sub> vs. V<sub>DD</sub>**



■ **Marking Specifications**

1. **TMSOP-8**



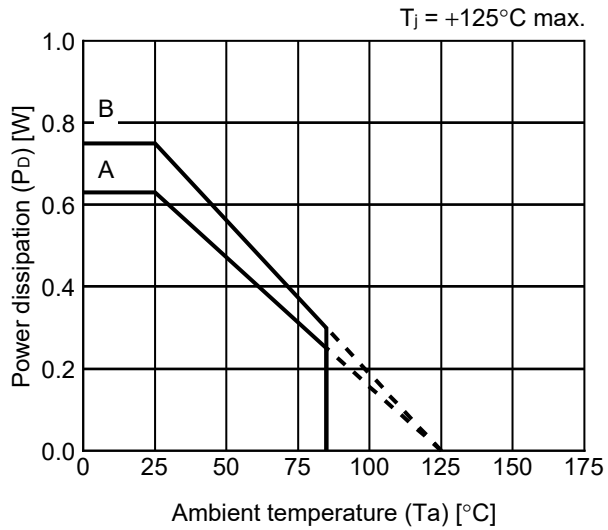
- (1): Blank
- (2) to (4): Product code (Refer to **Product name vs. Product code**)
- (5): Blank
- (6) to (8): Lot number

**Product name vs. Product code**

Product Name	Product Code		
	(2)	(3)	(4)
S-8215CAA-K8T2U7	H	Y	A
S-8215CAB-K8T2U7	H	Y	B

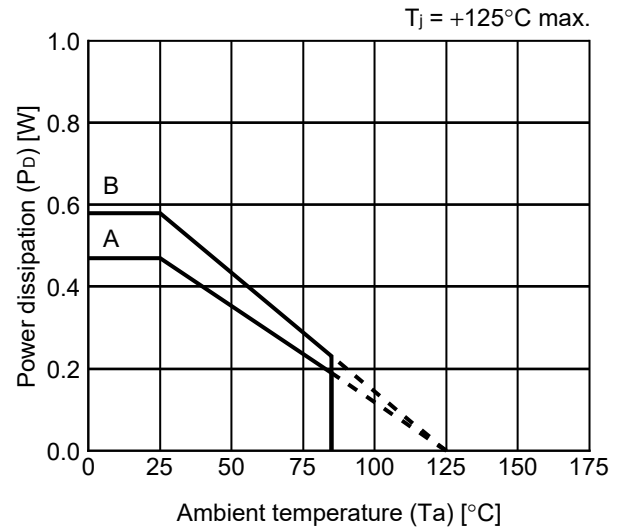
■ **Power Dissipation**

**TMSOP-8**



Board	Power Dissipation ( $P_D$ )
A	0.63 W
B	0.75 W
C	—
D	—
E	—

**SNT-8A**



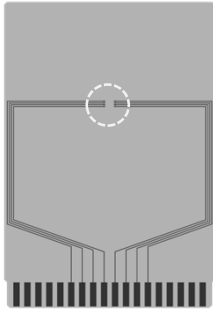
Board	Power Dissipation ( $P_D$ )
A	0.47 W
B	0.58 W
C	—
D	—
E	—



# TMSOP-8 Test Board

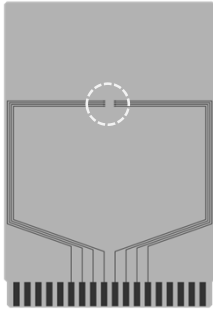
(1) Board A

 IC Mount Area



Item	Specification	
Size [mm]	114.3 x 76.2 x t1.6	
Material	FR-4	
Number of copper foil layer	2	
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	-
	3	-
	4	74.2 x 74.2 x t0.070
Thermal via	-	

(2) Board B



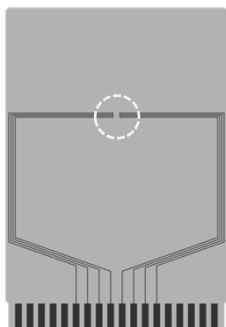
Item	Specification	
Size [mm]	114.3 x 76.2 x t1.6	
Material	FR-4	
Number of copper foil layer	4	
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via	-	

No. TMSOP8-A-Board-SD-1.0

# SNT-8A Test Board

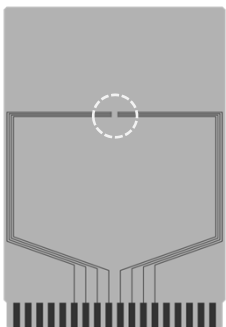
(1) Board A

 IC Mount Area



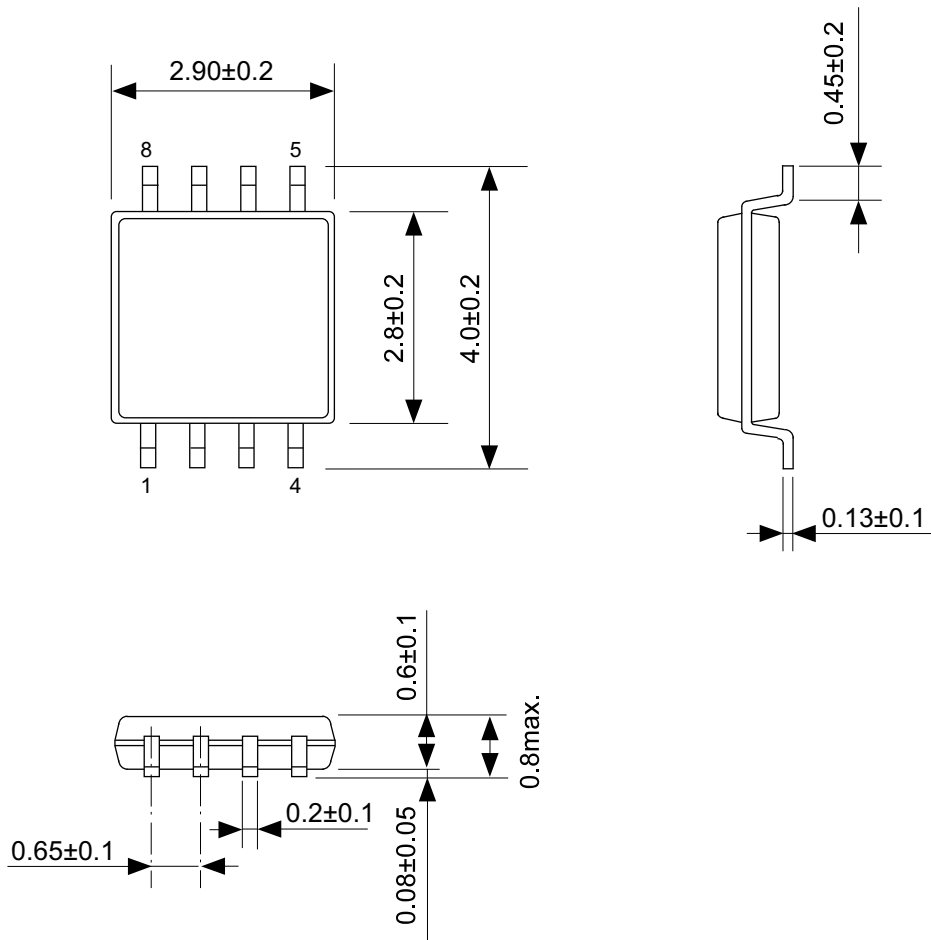
Item	Specification	
Size [mm]	114.3 x 76.2 x t1.6	
Material	FR-4	
Number of copper foil layer	2	
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	-
	3	-
	4	74.2 x 74.2 x t0.070
Thermal via	-	

(2) Board B



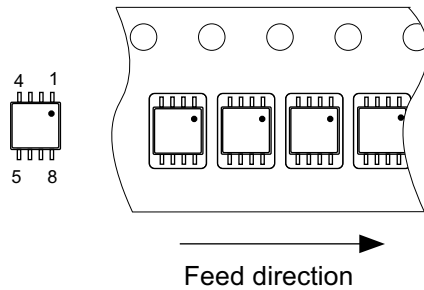
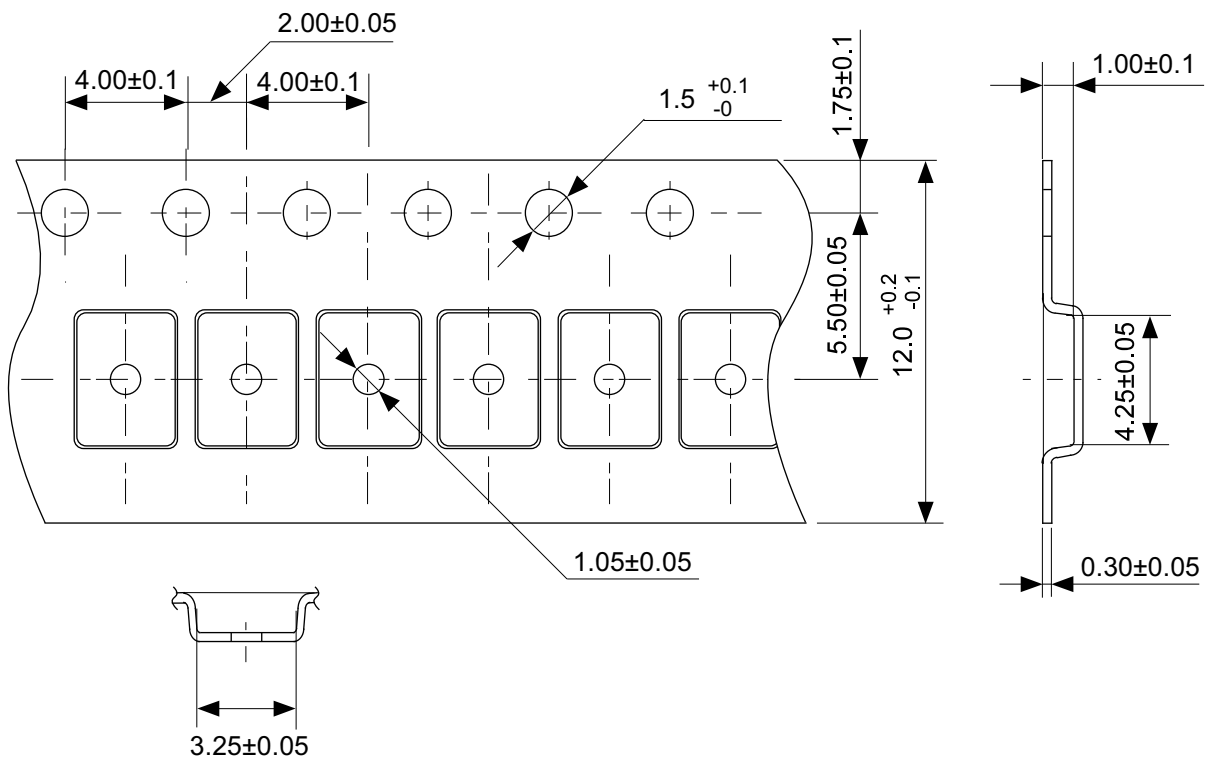
Item	Specification	
Size [mm]	114.3 x 76.2 x t1.6	
Material	FR-4	
Number of copper foil layer	4	
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via	-	

No. SNT8A-A-Board-SD-1.0



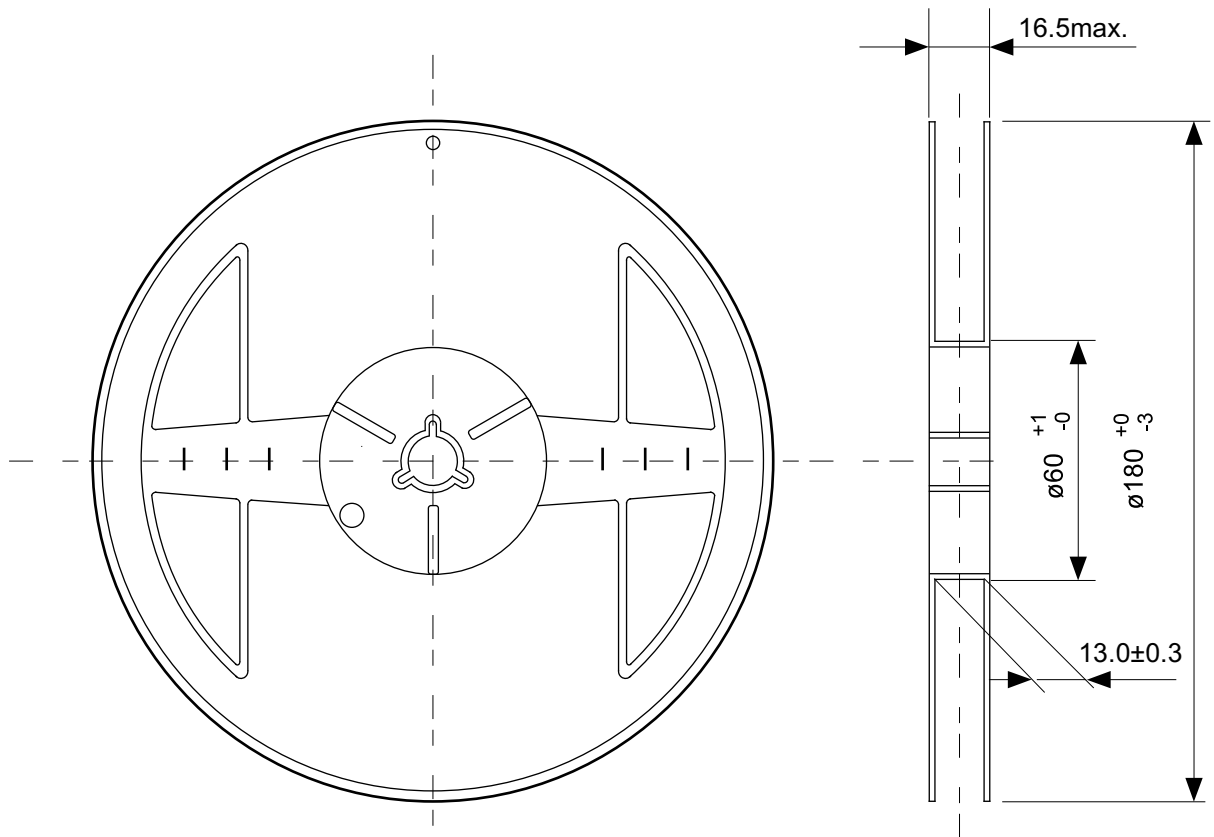
No. FM008-A-P-SD-1.2

TITLE	TMSOP8-A-PKG Dimensions
No.	FM008-A-P-SD-1.2
ANGLE	
UNIT	mm
<b>ABLIC Inc.</b>	

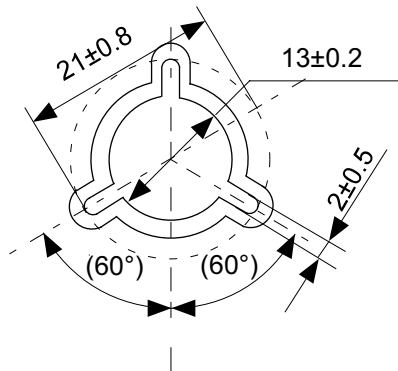


No. FM008-A-C-SD-2.0

TITLE	TMSOP8-A-Carrier Tape
No.	FM008-A-C-SD-2.0
ANGLE	
UNIT	mm
<b>ABLIC Inc.</b>	

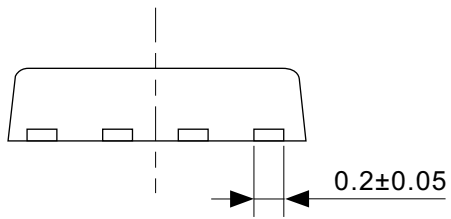
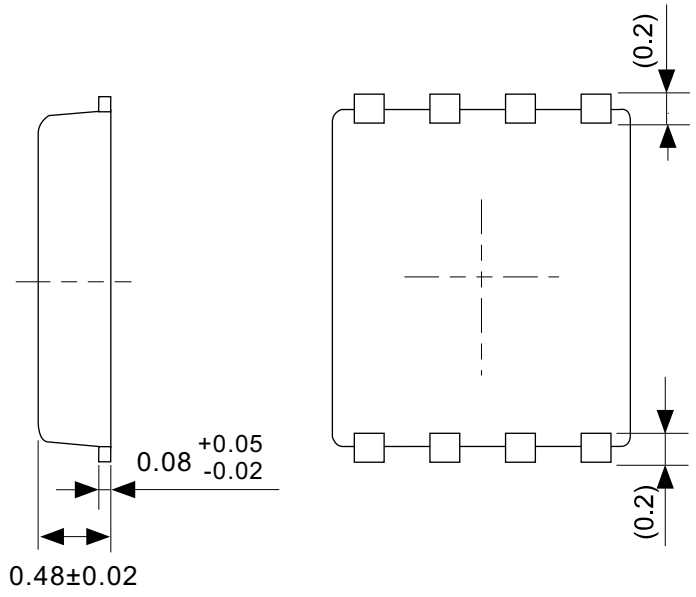
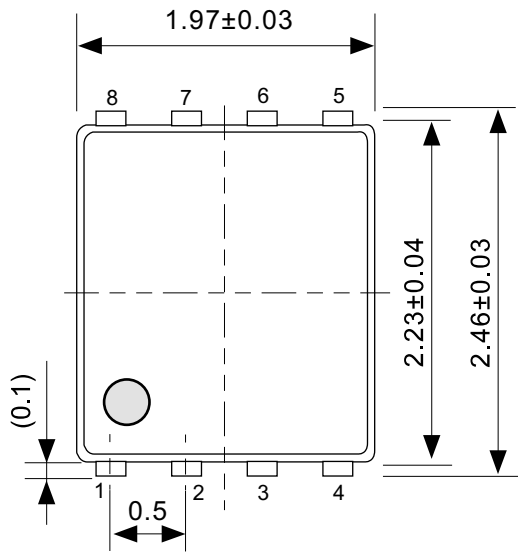


Enlarged drawing in the central part



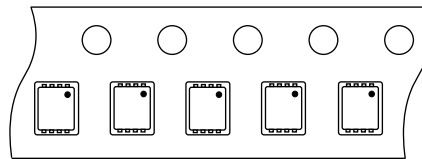
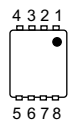
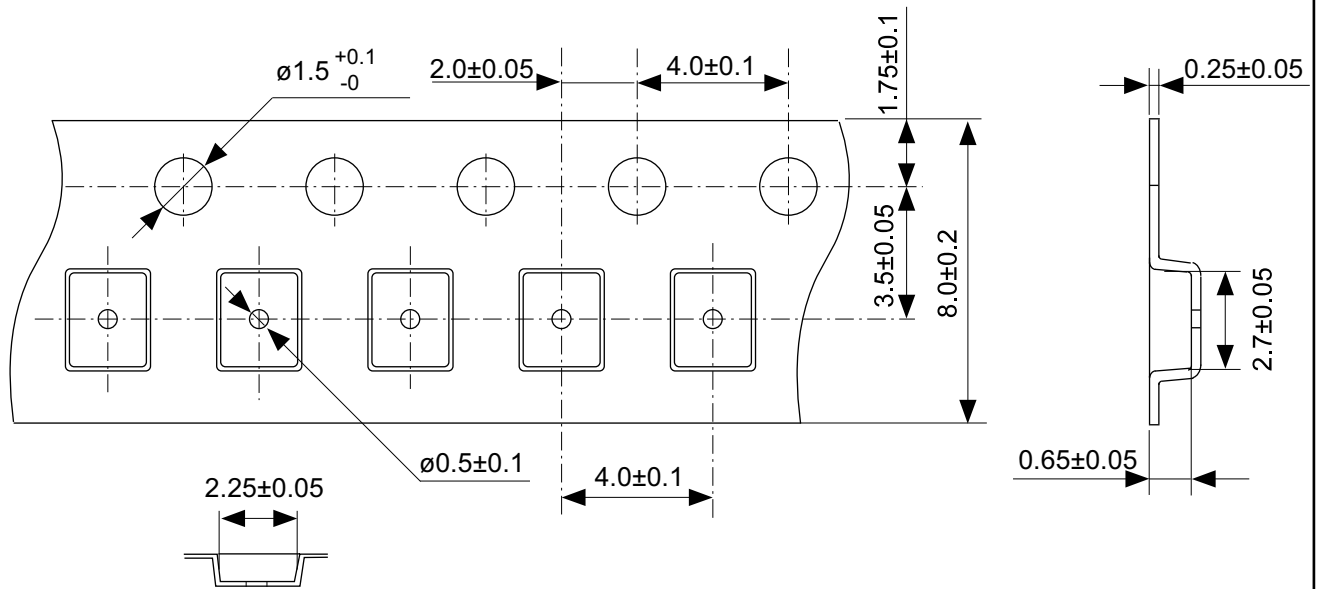
No. FM008-A-R-SD-1.0

TITLE	TMSOP8-A-Reel		
No.	FM008-A-R-SD-1.0		
ANGLE		QTY.	4,000
UNIT	mm		
<b>ABLIC Inc.</b>			



No. PH008-A-P-SD-2.1

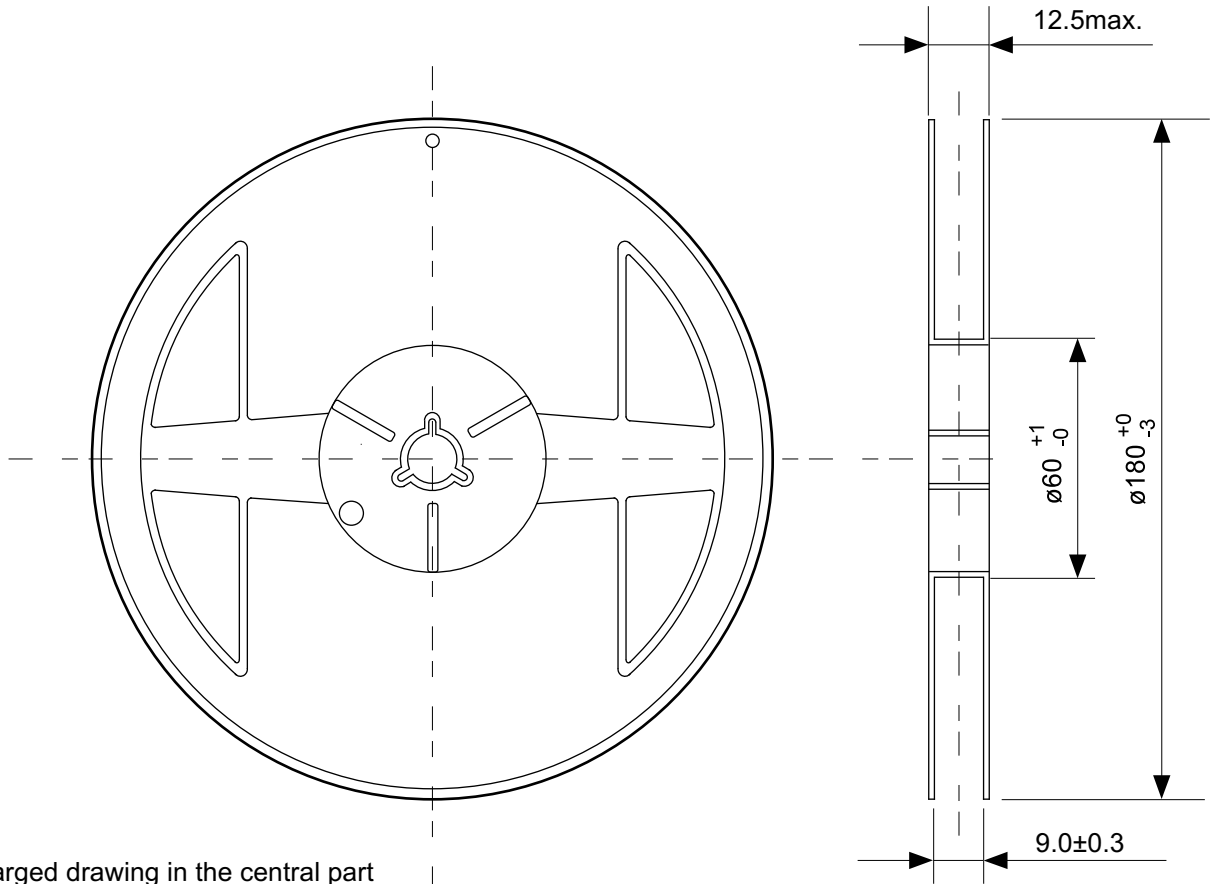
TITLE	SNT-8A-A-PKG Dimensions
No.	PH008-A-P-SD-2.1
ANGLE	
UNIT	mm
<b>ABLIC Inc.</b>	



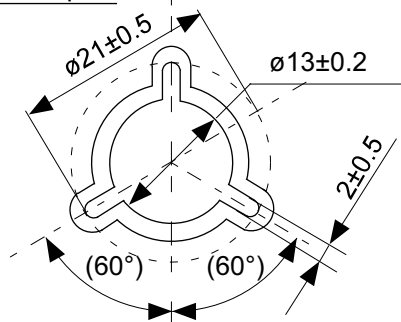
→  
Feed direction

No. PH008-A-C-SD-2.0

TITLE	SNT-8A-A-Carrier Tape
No.	PH008-A-C-SD-2.0
ANGLE	
UNIT	mm
<b>ABLIC Inc.</b>	



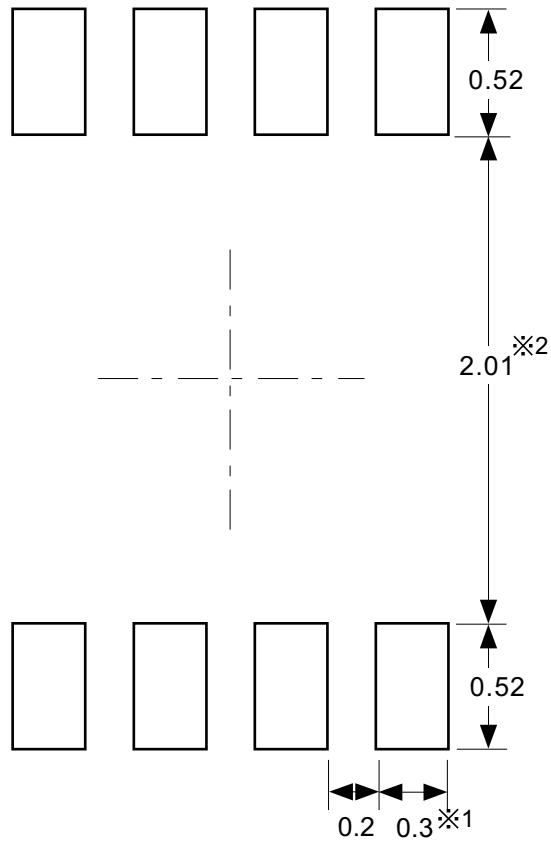
Enlarged drawing in the central part



No. PH008-A-R-SD-1.0

TITLE	SNT-8A-A-Reel		
No.	PH008-A-R-SD-1.0		
ANGLE		QTY.	5,000
UNIT	mm		
<b>ABLIC Inc.</b>			





※1. ランドパターンの幅に注意してください (0.25 mm min. / 0.30 mm typ.).  
 ※2. パッケージ中央にランドパターンを広げないでください (1.96 mm ~ 2.06 mm)。

- 注意
1. パッケージのモールド樹脂下にシルク印刷やハンダ印刷などしないでください。
  2. パッケージ下の配線上のソルダーレジストなどの厚みをランドパターン表面から0.03 mm以下にしてください。
  3. マスク開口サイズと開口位置はランドパターンと合わせてください。
  4. 詳細は“SNTパッケージ活用の手引き”を参照してください。

※1. Pay attention to the land pattern width (0.25 mm min. / 0.30 mm typ.).  
 ※2. Do not widen the land pattern to the center of the package (1.96 mm to 2.06mm).

- Caution**
1. Do not do silkscreen printing and solder printing under the mold resin of the package.
  2. The thickness of the solder resist on the wire pattern under the package should be 0.03 mm or less from the land pattern surface.
  3. Match the mask aperture size and aperture position with the land pattern.
  4. Refer to "SNT Package User's Guide" for details.

※1. 请注意焊盘模式的宽度 (0.25 mm min. / 0.30 mm typ.).  
 ※2. 请勿向封装中间扩展焊盘模式 (1.96 mm ~ 2.06 mm)。

- 注意
1. 请勿在树脂型封装的下面印刷丝网、焊锡。
  2. 在封装下、布线上的阻焊膜厚度 (从焊盘模式表面起) 请控制在 0.03 mm 以下。
  3. 钢网的开口尺寸和开口位置请与焊盘模式对齐。
  4. 详细内容请参阅 "SNT 封装的应用指南"。

No. PH008-A-L-SD-4.1

TITLE	SNT-8A-A -Land Recommendation
No.	PH008-A-L-SD-4.1
ANGLE	
UNIT	mm
<b>ABLIC Inc.</b>	

## Disclaimers (Handling Precautions)

1. All the information described herein (product data, specifications, figures, tables, programs, algorithms and application circuit examples, etc.) is current as of publishing date of this document and is subject to change without notice.
2. The circuit examples and the usages described herein are for reference only, and do not guarantee the success of any specific mass-production design.  
ABLIC Inc. is not liable for any losses, damages, claims or demands caused by the reasons other than the products described herein (hereinafter "the products") or infringement of third-party intellectual property right and any other right due to the use of the information described herein.
3. ABLIC Inc. is not liable for any losses, damages, claims or demands caused by the incorrect information described herein.
4. Be careful to use the products within their ranges described herein. Pay special attention for use to the absolute maximum ratings, operation voltage range and electrical characteristics, etc.  
ABLIC Inc. is not liable for any losses, damages, claims or demands caused by failures and / or accidents, etc. due to the use of the products outside their specified ranges.
5. Before using the products, confirm their applications, and the laws and regulations of the region or country where they are used and verify suitability, safety and other factors for the intended use.
6. When exporting the products, comply with the Foreign Exchange and Foreign Trade Act and all other export-related laws, and follow the required procedures.
7. The products are strictly prohibited from using, providing or exporting for the purposes of the development of weapons of mass destruction or military use. ABLIC Inc. is not liable for any losses, damages, claims or demands caused by any provision or export to the person or entity who intends to develop, manufacture, use or store nuclear, biological or chemical weapons or missiles, or use any other military purposes.
8. The products are not designed to be used as part of any device or equipment that may affect the human body, human life, or assets (such as medical equipment, disaster prevention systems, security systems, combustion control systems, infrastructure control systems, vehicle equipment, traffic systems, in-vehicle equipment, aviation equipment, aerospace equipment, and nuclear-related equipment), excluding when specified for in-vehicle use or other uses by ABLIC, Inc. Do not apply the products to the above listed devices and equipments.  
ABLIC Inc. is not liable for any losses, damages, claims or demands caused by unauthorized or unspecified use of the products.
9. In general, semiconductor products may fail or malfunction with some probability. The user of the products should therefore take responsibility to give thorough consideration to safety design including redundancy, fire spread prevention measures, and malfunction prevention to prevent accidents causing injury or death, fires and social damage, etc. that may ensue from the products' failure or malfunction.  
The entire system in which the products are used must be sufficiently evaluated and judged whether the products are allowed to apply for the system on customer's own responsibility.
10. The products are not designed to be radiation-proof. The necessary radiation measures should be taken in the product design by the customer depending on the intended use.
11. The products do not affect human health under normal use. However, they contain chemical substances and heavy metals and should therefore not be put in the mouth. The fracture surfaces of wafers and chips may be sharp. Be careful when handling these with the bare hands to prevent injuries, etc.
12. When disposing of the products, comply with the laws and ordinances of the country or region where they are used.
13. The information described herein contains copyright information and know-how of ABLIC Inc. The information described herein does not convey any license under any intellectual property rights or any other rights belonging to ABLIC Inc. or a third party. Reproduction or copying of the information from this document or any part of this document described herein for the purpose of disclosing it to a third-party is strictly prohibited without the express permission of ABLIC Inc.
14. For more details on the information described herein or any other questions, please contact ABLIC Inc.'s sales representative.
15. This Disclaimers have been delivered in a text using the Japanese language, which text, despite any translations into the English language and the Chinese language, shall be controlling.

2.4-2019.07